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Covalency, double-counting and the metal-insulator phase diagram in transition metal oxides

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Dynamical mean field theory calculations are used to show that for stoichiometric, late transition-metal-oxides a critical variable for the Mott/charge-transfer transition is the number of d-electrons, which is determined by charge transfer from oxygen ions. Insulating behavior is found only for a very narrow range of d-occupancy, irrespective of the Coulomb repulsion. For representative Ni and Cu-based transition metal oxides, density functional band calculations yield d occupancies very far from the values needed to sustain an insulating phase, indicating either that density functional theory fails to predict the physical d occupancy or that the conventional Mott/charge-transfer concept does not solely account for the observed insulating behavior in these systems.

I. INTRODUCTION

The strong electronic correlations characteristic of transition metal oxides pose a problem of long-standing interest[1,2] and great current importance[3–7]. In transition metal oxides the important low energy electronic states are derived from the transition metal d-orbitals. In a simple ionic picture the ground state corresponds to a d^n configuration for each transition metal ion, with d-electron number n depending on material. The correlation energy cost involved in changing the d-occupancy is conventionally denoted by U, is defined as $U = E[d^{n+1}] + E[d^{n-1}] - 2E[d^n]$ and is typically large. In a groundbreaking paper Mott[1] argued if U were large enough relative to the bandwidth then electron repulsion would prohibit conduction, at least at integer valence.

Mott's concept was refined in an important way by Zaanen, Sawatzky and Allen[8] who noted that correlated electron materials of interest typically contain ligands (for example the O atoms in transition metal oxides) which are close enough in energy to the chemical potential that one must also consider the transfer of an electron from a ligand to a transition metal site. Ref. 8 defined the charge transfer energy $E_{CT} = E[d^{n+1}] - E[d^n] - \varepsilon_p$ with $-\varepsilon_p$ the energy needed to create a hole in a ligand orbital and demonstrated that if U were large but $E_{CT} < U$ then the physics would be controlled by E_{CT} with U playing a relatively minor role. Implicit in this argument is a neglect of correlations on the oxygen sites; the justification is that the number of ligands is large enough and the hole density on the ligands small enough that configurations involving doubly occupied oxygen sites may be neglected. The resulting 'charge transfer insulator' paradigm is central to the conventional understanding[2] of the physics of transition metal oxides.

While density functional band theory (DFT)[9] is the work-horse of materials science, theoretical study of charge transfer insulators and other correlated electron materials requires methods which include additional correlations. Such "beyond DFT" methodologies require the identification of a set of orbitals whose correlations are to be treated more accurately and a prescription for embedding the correlated orbitals into the full electronic structure. Two widely used examples are the "DFT+U"[10] and "DFT+DMFT"[3,4] approaches. To date, when these methods are applied to transition metal oxides the correlated orbitals are chosen to be the transition metal d-levels. An important aspect of the the DFT+U and DFT+DMFT approaches is the 'double counting correction'[10–12], which removes correlation contributions from the DFT single-particle energies. The double-counting correction plays a particularly crucial role in charge transfer insulators because it affects the value of the charge transfer energy which is crucial to the physics. However, determining the double counting correction has proven problematic. Different prescriptions have been proposed[10–12], but there is no consensus on what is the correct procedure.

In this paper we argue that the double counting problem should be recast as a problem of determining the occupancy of the correlated orbitals. Expressing the problem in this way reveals a fundamental and apparently previously unnoticed dichotomy in the materials theory of late transition metal oxides such as the high T_c cuprates: either the d-occupancy is very different from that predicted by density functional band theory or the materials are very far from the Mott-Zaanen-Sawatzky-Allen metal-charge transfer insulator phase boundary. The first alternative would be surprising because the present implementations of density functional band theory, while not exact, are generally believed to provide reasonable good approximations to the electron density. The second alternative challenges the currently prevailing theoretical paradigm that the physics of cuprates is controlled by the Mott/charge-transfer transition. Our results also highlight a difficulty with the "DFT+DMFT" approach to transition metal oxides[3,4]: the physics predicted by this method is to a large degree controlled by the choice made for the double-counting correction.

II. THEORETICAL APPROACH

The approach we take is based on the "p-d" model, accepted in the literature[2,8,13] as a reliable description of transition metal oxides. The model includes correlated ("d") orbitals with appropriate on-site interactions, ligand (oxygen) orbitals (assumed uncorrelated because the hole density is small) and the relevant hybridizations. It may be written as

$$H = H_d + H_{hyb} + H_{ligand} \tag{1}$$

The Hamiltonian for the correlated ("d") subspace is

$$H_d = \sum_{i,a,\sigma} \varepsilon_d^a d^\dagger_{ia\sigma} d_{ia\sigma} + \frac{U}{2}\hat{N}_d^i\left(\hat{N}_d^i - 1\right) + H_J \tag{2}$$

with $d^\dagger_{ia\sigma}$ creating an electron in orbital a and spin σ on site i, $\hat{N}_d^i = \sum_{a\sigma} d^\dagger_{ia\sigma} d_{ia\sigma}$ the number operator for d electrons on site i and H_J representing the additional 'Hunds-rule' interactions which give the multiplet structure at fixed N_d (for explicit forms see e.g. Ref. 2). The localized nature of the d orbitals means that H_J interaction terms are given by measured gas-phase values, which agree with calculations[14]. The 'charging energy' U is renormalized significantly by screening and is less well established theoretically although interesting results have appeared[14]. In this paper we explore a range of U but we emphasize that in the charge transfer regime of principal interest here the precise value of U is not important as long as it is large. The model neglects interactions on the oxygen sites, on the grounds that the number of holes per O site is low. While the question of the importance of the oxygen U should be reexamined with modern methods, this issue is beyond the scope of this paper.

H_{ligand} and H_{hyb} describe the embedding of the correlated orbitals into the broader electronic structure and it is generally accepted[3,4] that reasonable estimates can be obtained from density functional band calculations, for example via the use of maximally localized Wannier function techniques with a suitable energy window.[11,15]

The crucial model parameter is the difference $\Delta = \varepsilon_p - \varepsilon_d$ between an average ligand on-site energy ε_p and the orbitally averaged d level energy $\varepsilon_d = \sum_a \varepsilon_d^a / n_{orb}$. Solution of the many-body model yields a physical charge transfer energy E_{CT} which depends on Δ and on the many-body interactions. A direct fit of the quadratic parts of Eq. 1 to a density functional calculation yields $E_{CT} = \Delta$; this value includes the density functional approximation to the interaction contributions, which are also incorporated in the solution of the many-body model. Thus it has been recognized for many years that to obtain the ε_d in Eq. 1 a "double counting correction" must be applied to the band theory estimate[10]. Different prescriptions for the double counting correction have been proposed[10–12], but no clear consensus has emerged. We investigate a range of Δ here.

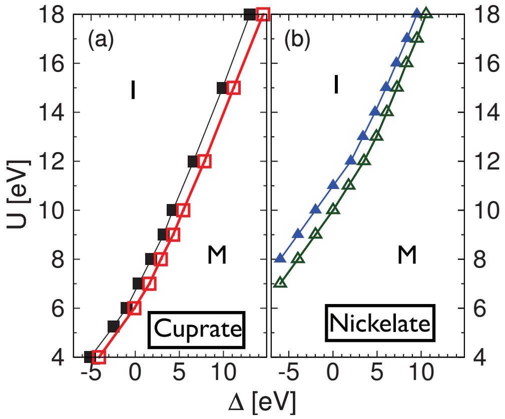

FIG. 1: (Color online) Metal-insulator phase diagram of model of high T_c cuprates (left panel) and rare-earth nickelates (right panel) in plane of $d-d$ on-site Coulomb interaction strength U and $d-p$ charge-transfer energy Δ. Filled symbols: limit Δ_{c2} of stability of metallic (M) phase. Open symbols: limit Δ_{c1} of stability of insulating (I) phase

To solve Eq. 1 we use the single-site dynamical mean field approximation[16] with the 'matrix' hybridization-expansion solver introduced in 17. Some results were cross-checked by the exact diagonalization method[18]. The single-site approximation is generally accepted as containing the essence of the Mott and charge-transfer metal-insulator transition physics and is widely used in "DFT+DMFT' studies of real materials[3,4]. Multi-site ("cluster") methods, which are prohibitively computationally expensive for multiband models with rotationally invariant interactions, provide a picture which is different in detail[19] but confirm that the single-site approximation captures the important high energy physics of the metal-insulator transition. In particular a reasonable working definition of whether or not a material is "strongly correlated" is whether the stoichiometric compound is on the metallic or insulating side of the single-site DMFT phase boundary[13,20].

We compute the behavior of two representative classes of charge-transfer materials, namely the layered high-T_c cuprates such as La_2CuO_4 and the pseudocubic rare-earth nickelates such as $LaNiO_3$. For La_2CuO_4 we use the standard "three-band" model with one d orbital per unit cell (representing the Cu $d_{x^2-y^2}$ orbital) and two p orbitals (representing the p_σ orbitals on the two planar oxygen ions). The $Cu-O$ and $O-O$ hoppings that make up $H_{hyb}+H_{ligand}$ are obtained from band structure calculations[13,21]. There is general agreement on the Cu_d-

O_{p_σ} hopping parameter $t_{pd} \approx 1.6eV$; different oxygen-oxygen hoppings are obtained by different workers but we have found that the behavior of the model does not in fact depend much on which value is chosen[22]. Because we consider only one d orbital in the cuprate case the only interaction is the Hubbard U. For $LaNiO_3$ we used a model with two d orbitals per unit cell, representing the x^2-y^2 and $3z^2-r^2$ states, as well as the O_{p_σ} orbitals on all three nearest-neighbor oxygen ions. We took the hybridization and ligand parameters from the GGA band calculations of Ref 23 (which we have verified are consistent with those arising from fitting the DFT results with maximally localized Wannier functions defined over the energy region $3eV$ above to $7eV$ below the chemical potential containing the p and d bands). We included the full Slater-Kanamori interactions in the e_g manifold[2] and set the exchange term J to 0.5 eV. In each case we fix the total number of electrons to correspond to the stoichiometric compound: one hole per unit cell in cuprates and three holes per unit cell in the nickelates.

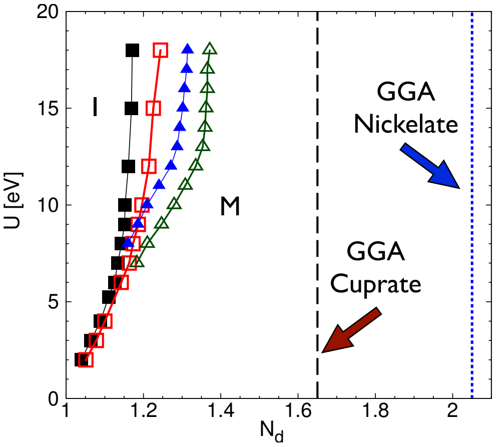

FIG. 2: (Color online) Metal-insulator phase diagram indicating limit of stability of metallic phase $N_{d,c2}$ (solid symbols), limit of stability of insulating phase $N_{d,c1}$ (open symbols) along with vertical lines indicating band theory estimates of N_d for model of high T_c cuprates (black and red squares, and black dashed line) and nickelates (blue and green triangles, and blue dotted line).

III. RESULTS

The two panels of Fig. [1] plot the metal insulator phase diagrams calculated for the two models in terms of the traditional variables of interaction strength U and d-p energy difference Δ. The left panel agrees with results previously presented in the literature for cuprates[22,24]. The corresponding results for nickelates shown in the right panel have not been previously presented. In single-site dynamical mean field theory the metal insulator transition is first order and is characterized by two spinodal lines: $U_{c1}(\Delta_{c1})$ where the insulating phase loses stability and a slightly different value $U_{c2}(\Delta_{c2})$ at which the metallic phase loses stability[16]. We present both lines, however we note that the U_{c2} phase boundary has a strong temperature dependence which is computationally very expensive to capture.

In Fig. 2 we replot the results in the plane of U and d-occupancy N_d with Δ as an implicit parameter. In the cuprates all of the d orbitals are filled except $d_{x^2-y^2}$ and we measure N_d with respect to the d^8 core s $0 \leq N_d \leq 2$ with the physical range being $1 \leq N_d \leq 2$. In the nickelates all d-orbitals are filled except the $d_{x^2-y^2}$ and $d_{3z^2-r^2}$ and we measure N_d with respect to the d^6 core so $0 \leq N_d \leq 4$ with the physical range being $1 \leq N_d \leq 4$. The replotted results are seen to have a remarkably simple structure. At small U the phase boundaries extrapolate linearly to $U=0$, $N_d=1$ because as $N_d \rightarrow 1$ the d bands become far removed from the p bands so both the d bandwidth and $N_d-1 \sim 1/\Delta$. However, for physically relevant U values the phase boundary is essentially vertical, and occurs at $N_d \sim 1.15-1.25$ in the two dimensional (cuprate) case and at $N_d \sim 1.25-1.35$ in the three dimensional (nickelate) case.

The simplicity of the $U-N_d$ phase diagram, along with the fact that the bare charge transfer energy Δ is a purely theoretically defined quantity which cannot be directly measured, identifies N_d as the critical variable for placing transition metal oxides on the metal-insulator phase diagram. Further evidence that N_d is the important parameter can be found in the electron spectral function (many-body density of states), obtained by maximum entropy analytical continuation from our imaginary time QMC data using the approach in Ref. 25 and shown for the nickelate case in Fig. [3] for several different combinations of interaction strength and charge transfer energy. The similarity of spectra with similar N_d but different Δ and U is evident.

IV. CONCLUSIONS

N_d has a precise meaning in the model defined by Eq. 1 but different definitions are available in band theory, including computing the charge density from orbitally projected wave functions within a sphere of a given radius, and constructing maximally localized Wannier functions within some appropriately chosen energy window[11,15]. We have used literature values for the cuprates[13,21] and obtained N_d for $LaNiO_3$ from the maximally localized Wannier function construction defined above; the results agree within 10% with the N_d obtained from the sphere construction and reported in Ref. 23. The results are $N_d \approx 1.65$ for cuprates (indicated by dashed line in Fig. 2) and $N_d \sim 2$ for nickelates (indicated by dotted line in Figs. 2). For both materials, the N_d values we obtain are so much higher than the critical values needed to drive the metal-insulator transition in single-site dynamical mean field theory that any ambiguities in the calculational definition of N_d are not relevant.

However, the density functional results may not be definitive. While the approximate DFT implementations in use today are believed to produce accurate estimates of many electronic properties[9], there is no solid-state benchmark for the quantitative reliability of the results of present state of the art functionals and some experimental results indicate that density functional methods overestimate covalency[26]. Thus it might be that density functional results for N_d are substantially in error. This view is implicitly adopted in some of the DFT+DMFT literature. For example Ref.[13] models La_2CuO_4 using a double counting correction which shifts N_d from ~ 1.65 to ~ 1.1.

Experimental determination of the d valence is therefore desirable. Indirect measurements, for example of the transferred hyperfine couplings[27] or the magnetic form factor in ordered states[28] have indicated very strong covalency effects in cuprates. The estimates given in these papers are $N_d \sim 1.6$, comparable to the band theory values. A more direct approach would be to detect the density of holes on oxygen via resonant X-ray scattering techniques as in Refs. 7,29. As indicated in Fig. 3, spectroscopic measurements of the relative position of p and d features in the many-body density of states would also be revealing. One particularly informative experiment would be a measurement of changes in the density across the $ReNiO_3$ series, to reveal the change in O-hole density. A systematic evaluation of the reliability of DFT estimates of transition metal-ligand covalency is also indicated.

However, if the DFT results for N_d are reasonable, then associating the observed behavior of transition metal oxides with the Mott/charge-transfer insulator paradigm becomes problematic. La_2CuO_4 is observed to be an insulator in experiment, and therefore if the d-occupancy predicted by DFT is not seriously in error, physics beyond simple Mott/charge-transfer picture must be invoked to drive the insulating state. For example, at moderate correlations a crucial effect of intermediate-ranged antiferromagnetic correlations has been found in cluster dynamical mean field and other approximations.[30–33] $LaNiO_3$ is a metal in experiment, consistent with our GGA+DMFT calculations based on the GGA N_d. However, replacing La by other rare earths drives a metal-insulator transition which is sometimes associated with the Mott transition. Changing the rare earth distorts the lattice, and it is possible that this distortion might change N_d, but we have verified that within GGA band theory the d-occupancy is nearly the same for $LuNiO_3$ in the experimental structure as it is for $LaNiO_3$. The results of this paper suggest that the observed insulating behavior is not solely determined by the Mott/charge-transfer phenomenon, but is instead associated with other physics, for example with the observed disproportionation in $Ni-O$ bond lengths. GGA +U calculations (see Ref. 34 and to be published) confirm this association.

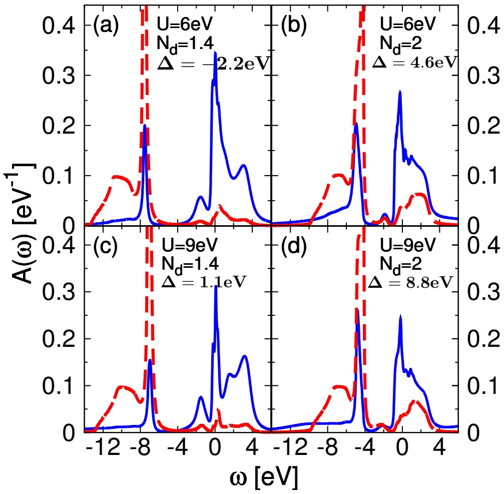

FIG. 3: (Color online) Local spectral functions for the nickelates. Solid blue lines show the d-density of states and the dashed red lines show the p-density of states. The parameters for different panels are indicated.

To summarize, in this paper we have identified the d-occupancy as a key variable for placing transition metal oxides in the Mott-Zaanen-Sawatzky-Allen metal-insulator phase diagram. We show that the conventional metal-insulator transition only occurs over a narrow range of d-occupancies, that a transition will not occur for sufficiently large d-occupancies, and that standard band theory techiques predict d occupancies which are deep in the metallic regime for La_2CuO_4 and $LaNiO_3$. While the notion of 'orbital' is not precisely definable in the solid-state context, ambiguities in the definition lead to uncertainties which are small on the scale of the difference between the DFT N_d and the phase boundary. Thus the observed insulating behavior of La_2CuO_4 indicates either that density functional band theory methods provide remarkably erroneous estimates of N_d or that some physics beyond the Mott/charge-transfer paradigm is required to explain the insulating behavior of this material. Our results have implications for 'beyond-DFT' theories of correlated electron materials. The beyond-DFT theories available to date typically require a definition of correlated orbitals which implies precisely defined orbital occupancies, and must introduce double-counting corrections. As we have shown, it is these double-counting corrections which fix the d-occupancy and therefore dictate the resulting physical behavior.

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